

Oral presentation | 21 Joint Session K | 21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"

[19p-224A-1~8]21.1 Joint Session K "Wide bandgap oxide semiconductor materials and devices"

Keisuke Ide(Tokyo Tech.), Shizuo Fujita(京大)

Wed. Sep 19, 2018 1:00 PM - 3:15 PM 224A (224-1)

△ : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼ : Both of Above

No Mark : None of Above

1:00 PM - 1:30 PM

▲[19p-224A-1][JSAP Paper Award Speech] Delta-doped β -gallium oxide field-effect transistor

Sriram Krishnamoorthy¹, Zhanbo Xia², Sanyam Bajaj², Mark Brenner², Siddharth Rajan² (1.Univ. of Utah, 2.Ohio State Univ.)

Keywords:JSAP Paper Award